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FDB15N50 N-Channel UniFET[™] MOSFET 500 V, 15 A, 380 mΩ

Features

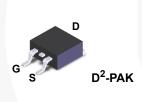
- Low gate charge ${\rm Q}_{\rm g}$ results in simple drive requirement (Typ. 33 nC)
- Improved Gate, avalanche and high reapplied dv/dt ruggedness
- Reduced $R_{DS(on)}$ (330m Ω (Typ.) @ V_{GS} = 10 V, I_D = 7.5 A)
- Reduced Miller capacitance and low Input capacitance (Typ. C_{rss} = 16 pF)
- Improved switching speed with low EMI
- 175°C rated junction temperature

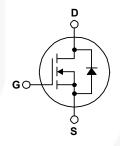
Description

UniFETTM MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.

Applications

- Lighting
- Uninterruptible Power Supply
- AC-DC Power Supply





Absolute Maximum Ratings $T_C = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	FDB15N50	Unit		
V _{DSS}	Drain to Source Voltage	500	V		
V _{GS}	Gate to Source Voltage	±30	V		
	Drain Current Continuous ($T_C = 25^{\circ}C$, $V_{GS} = 10V$)	15	А		
Ι _D	Continuous ($T_C = 100^{\circ}C$, $V_{GS} = 10V$)	11	А		
	Pulsed (Note 1)	60	А		
PD	Power dissipation Derate above 25°C	300 2	W W/ºC		
T _J , T _{STG}	Operating and Storage Temperature	-55 to 175	°C		
	Soldering Temperature for 10 seconds	300 (1.6mm from case)	°C		

Thermal Characteristics

Symbol	Parameter	FDB15N50	Unit	
$R_{ extsf{ heta}JC}$	Thermal Resistance Junction to Case, Max.	0.50	°C/W	
R_{\thetaJA}	Thermal Resistance Junction to Ambient, Max.	62	°C/W	

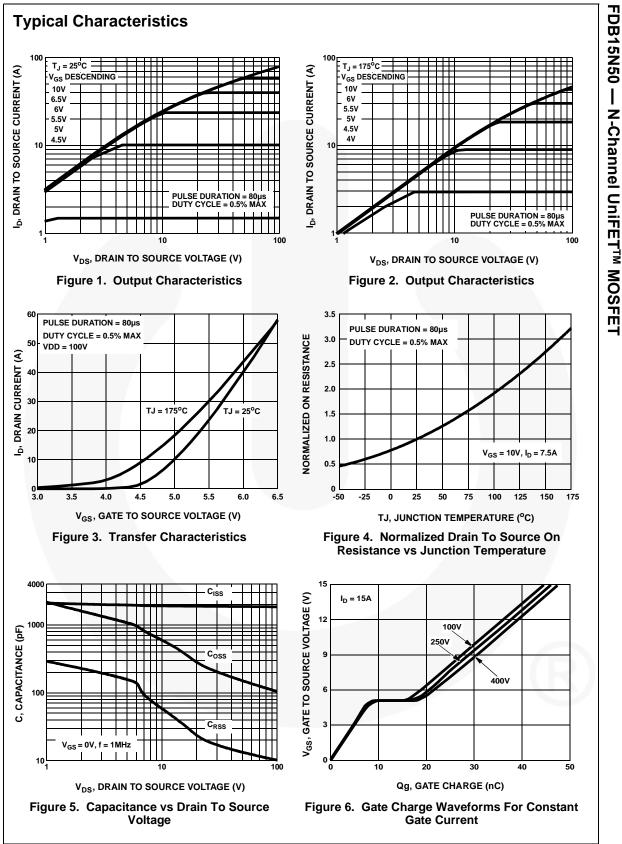
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November 2013

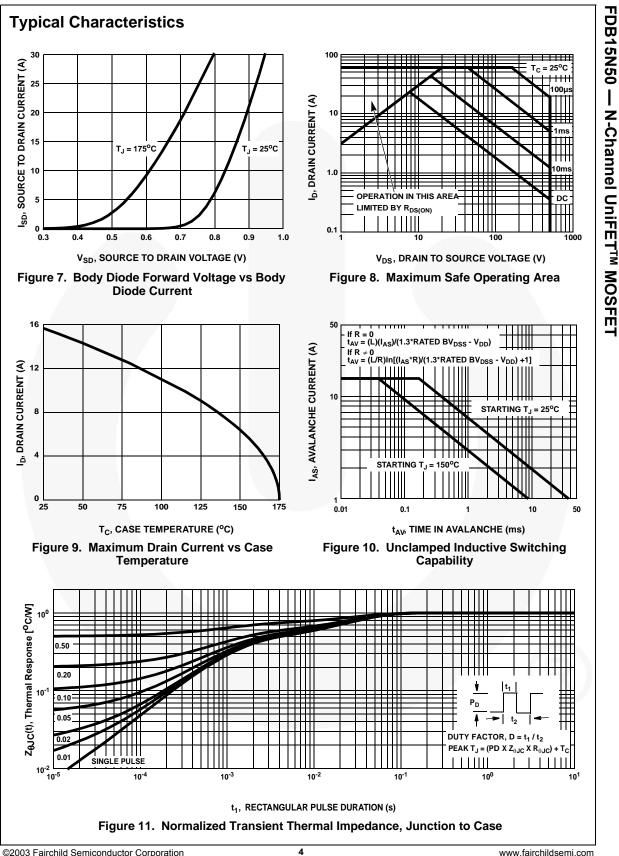
Symbol BvDSS Dra BvDSS Dra ΔBvDSS/ΔTJ Bra RDS(ON) Dra VGS(th) Ga IDSS Ga UGSS Ga Opnamics Ga	Characteria Para ain to Source Bro eakdown Voltage ain to Source Or te Threshold Vo ro Gate Voltage	eakdown Voltage Temp. Coefficie -Resistance	e ent	Test ($I_D = 250\mu A$, Reference t $I_D = 1mA$	Cone	ditions	24 Min 500	Тур	800 u	units Unit
Symbol BvDSS Dra BvDSS Dra ΔBvDSS/ΔTJ Bra RDS(ON) Dra VGS(th) Ga IDSS Ga Dynamics Ga	Para ain to Source Bro eakdown Voltage ain to Source Or te Threshold Vo ro Gate Voltage	eakdown Voltage Temp. Coefficie -Resistance	e ent	Test ($I_D = 250\mu A$, Reference t $I_D = 1mA$	Cone	ditions			Max	Unit
bitatics B _{VDSS} Dra AB _{VDSS} /∆T _J Bre R _{DS(ON)} Dra V _{GS(th)} Ga I _{DSS} Zer I _{GSS} Ga Dynamics g _{fs} For	ain to Source Bre eakdown Voltage ain to Source Or te Threshold Vo ro Gate Voltage	eakdown Voltag Temp. Coefficie -Resistance tage	ent	I _D = 250µA, Reference t I _D = 1mA	, V _G				Max	Unit
B _{VDSS} Dra ΔB _{VDSS} /ΔT _J Bre R _{DS(ON)} Dra V _{GS(th)} Ga I _{DSS} Zer I _{GSS} Ga Dynamics gfs For	eakdown Voltage ain to Source Or te Threshold Vo ro Gate Voltage	e Temp. Coefficie -Resistance Itage	ent	Reference t I _D = 1mA		_S = 0V	500			
B _{VDSS} Dra ΔB _{VDSS} /ΔT _J Bre R _{DS(ON)} Dra V _{GS(th)} Ga I _{DSS} Zer I _{GSS} Ga Dynamics gfs For	eakdown Voltage ain to Source Or te Threshold Vo ro Gate Voltage	e Temp. Coefficie -Resistance Itage	ent	Reference t I _D = 1mA		_S = 0V	500			
AB _{VDSS} /AT _J Bre R _{DS(ON)} Dra V _{GS(th)} Ga I _{DSS} Zer I _{GSS} Ga Pynamics g _{fs} For	eakdown Voltage ain to Source Or te Threshold Vo ro Gate Voltage	e Temp. Coefficie -Resistance Itage	ent	Reference t I _D = 1mA		5 = 01	000	-	-	V
R _{DS(ON)} Dra V _{GS(th)} Ga I _{DSS} Zer I _{GSS} Ga Pynamics g _{fs} For	ain to Source Or te Threshold Vo ro Gate Voltage	-Resistance tage	ent	$I_D = 1mA$		Beforence to 25%				
V _{GS(th)} Ga I _{DSS} Zer I _{GSS} Ga Dynamics g _{fs} For	te Threshold Vo ro Gate Voltage	tage					-	0.58	-	V/°C
I _{DSS} Zei I _{GSS} Ga Iynamics g _{fs} Foi	ro Gate Voltage			V _{GS} = 10V, I _D = 7.5A		-	0.33	0.38	Ω	
I _{GSS} Ga Dynamics g _{fs} For		Drain Current		$V_{DS} = V_{GS}, I_D = 250 \mu A$		2.0	3.4	4.0	V	
I _{GSS} Ga Dynamics g _{fs} For				$V_{DS} = 500 V$		$T_{C} = 25^{\circ}C$	-	-	25	μA
ynamics g _{fs} For	te to Source Lea			$V_{GS} = 0V$		$T_{C} = 150^{\circ}C$	-	-	250	μ
g _{fs} For		Gate to Source Leakage Current		$V_{GS} = \pm 30 V$	/		-	-	±100	nA
g _{fs} For										
013	rward Transcond	luctance		V _{DD} = 10V,	ln =	7.5A	10	-	-	s
	al Gate Charge			$V_{GS} = 10V,$	_		-	33	41	nC
5(- /	te to Source Ga			$V_{\rm GS} = 100$, $V_{\rm DS} = 400$ V			-	7.2	10	nC
3-	Gate to Drain "Miller" Charge			I _D = 15A		-	12	16	nC	
gu	urn-On Delay Time			V _{DD} = 250\	/		-	9		ns
u(0.1)	se Time	e Time n-Off Delay Time		$I_{\rm D} = 15$ A,	/,		-	5.4	-	ns
t _{d(OFF)} Tur	rn-Off Delay Tim			R _G = 6.2Ω,			-	26	-	ns
	Il Time			$R_D = 17\Omega$			-	5	-	ns
C _{ISS} Inp	out Capacitance					-	1850	-	pF	
C _{OSS} Ou	Output Capacitance			V _{DS} = 25V, V _{GS} = 0V, f = 1MHz		-	230	-	pF	
	verse Transfer C	apacitance		= 100112			-	16	-	pF
valanche C	haracteristic	S								
_	ngle Pulse Avala		Note 2)				760	- 1	-	mJ
	Avalanche Current						-	-	15	Α
	Diode Char	acteristics								
Lo Co	ntinuous Source			MOSFET symbol		ol 🧯	-	-	15	А
- (БС	ody Diode)	ront		showing the		. (5 7)				<u> </u>
I _{SM} (Bo	lsed Source Cur ody Diode)			p-n junction diode.		-	-	60	A	
V _{SD} So	urce to Drain Die	ode Voltage		I _{SD} = 15A			-	0.86	1.2	V
	verse Recovery			$I_{SD} = 15A$, $di_{SD}/dt = 100A/\mu s$		-	470	730	ns	
Q _{RR} Re	Reverse Recovered Charge			I_{SD} = 15A, di _{SD} /dt = 100A/µs		-	5	6.6	μC	

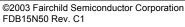
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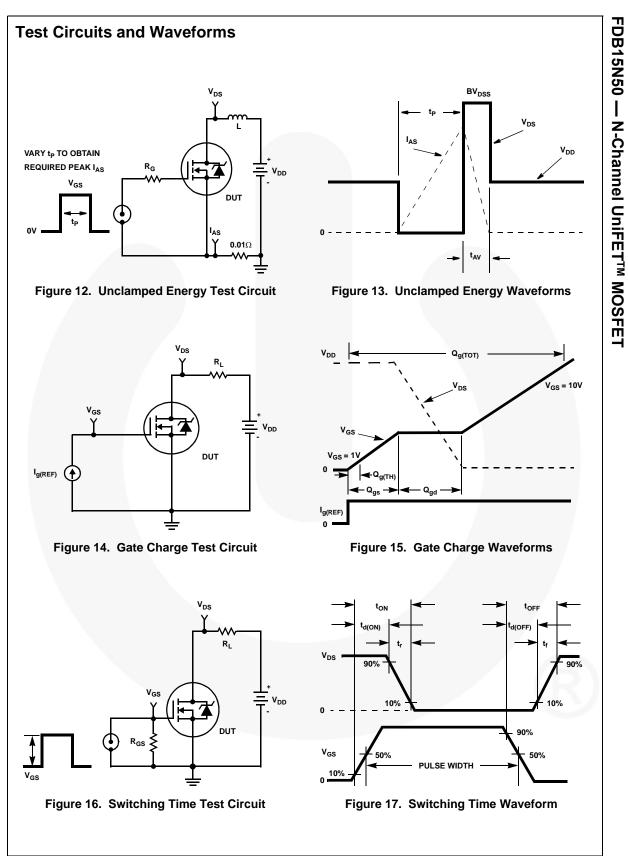


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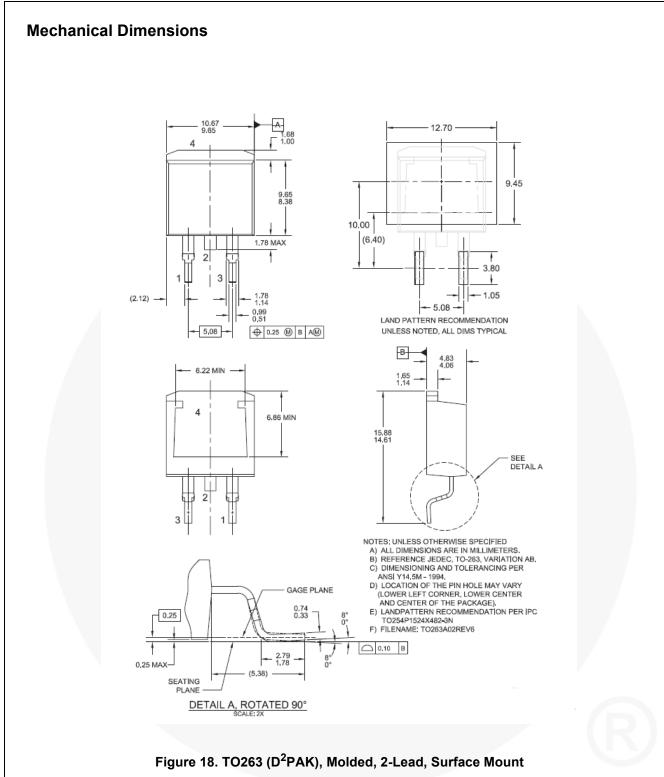
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FDB15N50 — N-Channel UniFET[™] MOSFET



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